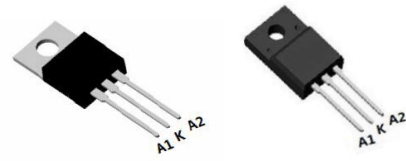
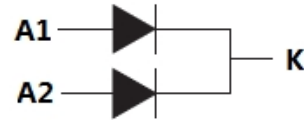
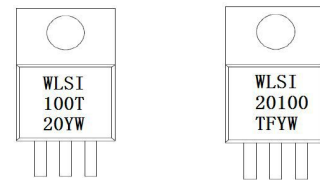


WSB20100T/WSB20100TF
Power Schottky Barrier Rectifier
www.sh-willsemi.com
Features

- 2x10A average rectified forward current
- Low forward voltage and Low leakage current
- Excellent high junction temperature stability
- High forward surge capability


TO-220
TO-220F

Circuit
Applications

- High frequency switch model power supplies
- DC-DC Convertors, Power adapters


TO-220
TO-220F
Marking

Absolute maximum ratings				
Parameter		Symbol	Value	Unit
Reverse voltage (repetitive peak)		V_{RM}	100	V
Reverse voltage (DC)		V_R	100	V
Average rectified forward current	Per diode	I_F	10	A
	Per device	I_F	20	A
Peak Forward Surge Current ⁽¹⁾		I_{FSM}	100	A
Junction temperature		T_J	150	°C
Operating temperature		T_{opr}	-55 ~ 150	°C
Storage temperature		T_{stg}	-55 ~ 150	°C
Thermal Resistance Ratings				
Maximum Thermal Resistance Junction To case (Per leg)	TO-220	$R_{\theta JC}$	2.2	°C/W
	TO-220F		4.4	

Order information			
Device	Package	Marking	Units/Tube
WSB20100T-3/T	TO-220	WLSI100T20YW ⁽²⁾	50
WSB20100TF-3/T	TO-220F	WLSI20100TFYW ⁽³⁾	

Note 1 : Pulse Width=8.3ms, Single Sine Pulse

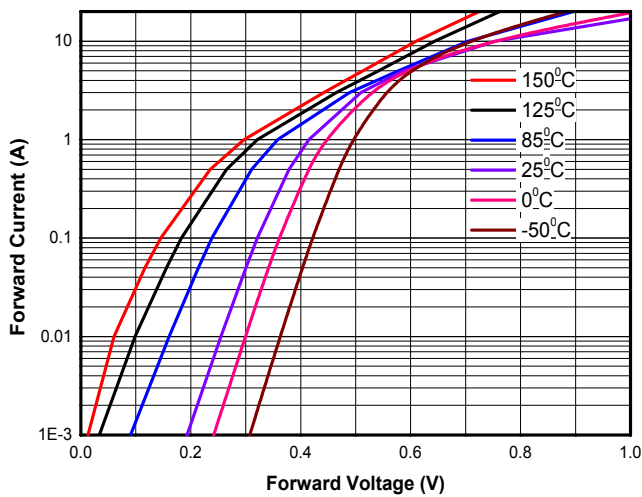
Note 2 : WLSI=Willsemi; 100T= Device code;20=Special Code; Y=Year; W=Week (A~z)

Note 3 : WLSI=Willsemi; 20100= Device code; TF=Special Code; Y=Year; W=Week (A~z)

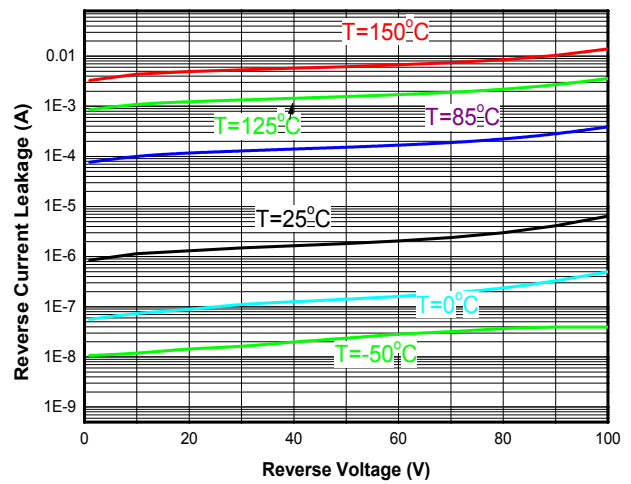
Electronics characteristics (T_A=25°C, Per diode)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	V _R	I _R =0.5mA	100			V
Forward voltage	V _F	I _F =10A			0.85	V
Reverse current	I _R	V _R =100V	-		0.1	mA
Junction capacitance	C _J	V _R =25V, F=1MHz	-	110		pF

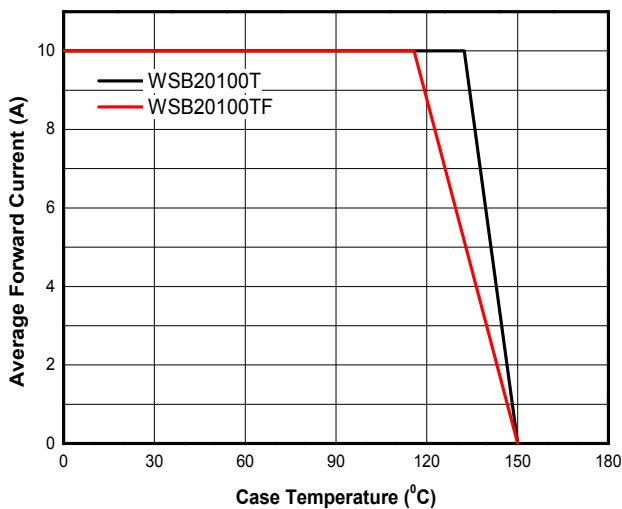
Typical characteristics (T_a=25°C, Per diode)



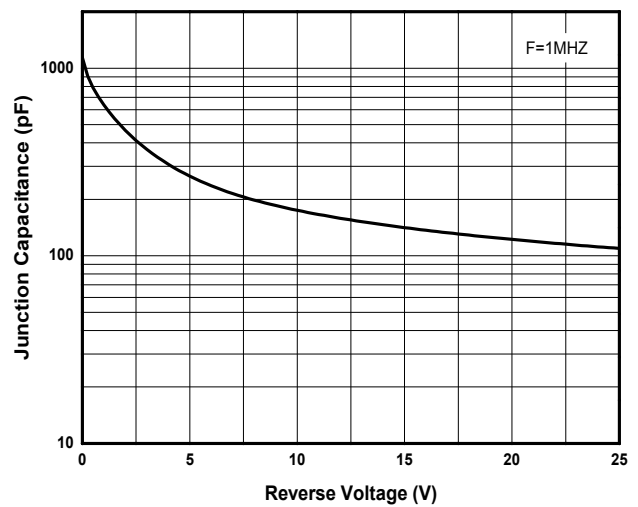
Forward voltage vs. Forward current



Reverse current vs. Reverse voltage

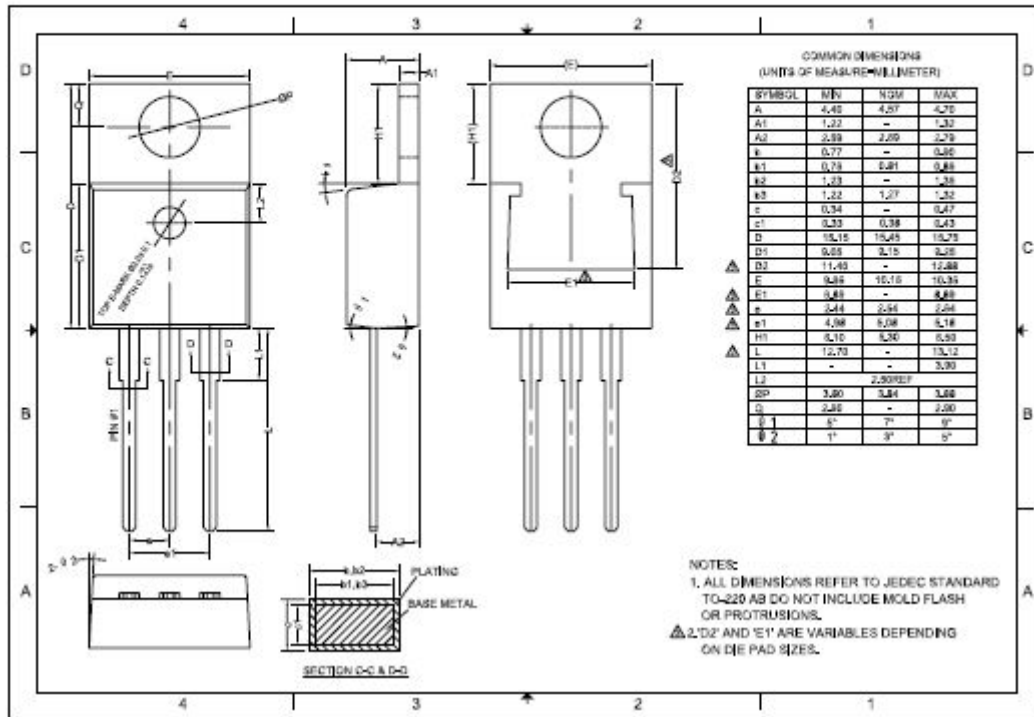


Forward Current Derating Curve



Junction capacitance vs. Reverse voltage

Package outline dimensions

TO-220

TO-220F
